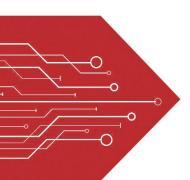
# MSKSEMI















**ESD** 

TVS

TSS

MOV

**GDT** 

**PLED** 

# Brodnet data speet

www.msksemi.com









#### **Features**

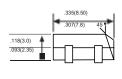
Ideal for printed circuit board

Reliable low cost construction utilizing molded plastic technique

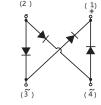
High temperature soldering guaranteed: 260°/10 seconds at 5

lbs., (2.3kg) tension

Small size, simple installation High surge current capability



### **Mechanical Data** Case: JEDEC DBS Molded plastic body Terminals: Solder plated, solderable per MIL-STD-750, Method 2026 Polarity: Polarity symbol marking on body



Dimensions in inches and (millimeters)

#### **REEL SPECIFICATION**

Mounting Position: Any Weight: 0.02 ounce, 0.4 grams

P/N	PKG	QTY
DB151S-DB157S	DBS	1500

## **Maximum Ratings And Electrical Characteristics**

Ratings at 25°C ambient temperature unless otherwisespecified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter			1S DB152S	DB153S	DB154S	DB155S	DB156S	DB157S	UNITS
Marking Code	SYMBOLS	DB151S							
Maximum repetitive peak reverse voltage	Vrrm	50	100	200	400	600	800	1000	V
Maximum RMS voltage	VRMS	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	VDC	50	100	200	400	600	800	1000	V
Maximum average forward rectified current at T <sub>C</sub> =40°C		1.5						А	
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)		50						А	
Maximum instantaneous forward voltage drop per leg at 1.5A		1.1						V	
Maximum DC reverse current T <sub>A</sub> =25°C at rated DC blocking voltage T <sub>A</sub> =100°C	lR	10 500					μΑ μΑ		
Operating temperature range	Τυ	-55 to +150			°C				
storage temperature range	Тѕтс	-55 to +150			°C				

NOTES:DBS for surface mount package.

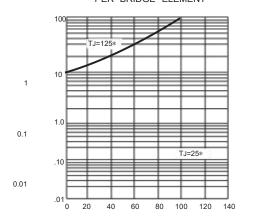
INSTANTANEOUS REVERSE CURRENT(\*A)

FIG. 1- MAXIMUN DERATING CURVE FOR OUTPUT RECTIFIED CURRENT 0.6 '(1.5mm 2.0 Opper Pa uls .51"x. 51" (13mmx13 mm) 1.5 1.0 0.5 0 20 140 150

AMBIENT TEMPERATURE, C

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT PEAK FORWARD CURRENT.(A) 50 Single sine wave (JED EC Meth od) 40 30 20 10 0 100 NUMBER OF CYCLES AT 60 Hz

FIG. 3-TYPICAL REVERSE CHARACTERISTICS PER BRIDGE ELEMENT



PERCENT OF RATED PEAK REVERSE VOLTAGE.(%)

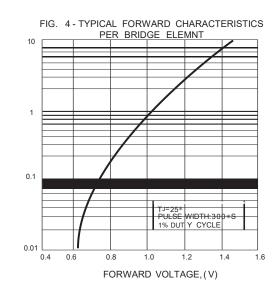
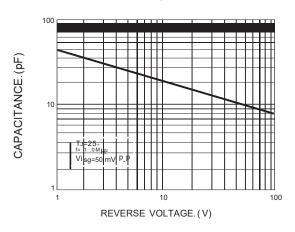


FIG. 3-TYPICAL JUNCTION CAPACITANCE PER BRIDGE ELEMENT

INSTANTANEOUS REVERSE CURRENT.(A)







- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specificationsof any andall MSKSEMI Semiconductor products described orcontained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringementsof intellectual property rights or other rightsof third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

## 单击下面可查看定价,库存,交付和生命周期等信息

>>MSKSEMI (美森科)